

BUK71/7905-40ATE

TrenchPLUS standard level FET

Rev. 01 — 20 August 2003

Product data

1. Product profile

1.1 Description

N-channel enhancement mode field-effect power transistor in a plastic package using TrenchMOS™ technology, featuring both very low on-state resistance and TrenchPLUS diodes for temperature sensing and ESD protection.

Product availability:

BUK7105-40ATE in SOT426 (D²-PAK)

BUK7905-40ATE in SOT263B (TO-220).

1.2 Features

- Integrated temperature sensor
- Electrostatic discharge protection
- Q101 compliant
- Standard level compatible.

1.3 Applications

- Variable Valve Timing for engines
- Electrical Power Assisted Steering.

1.4 Quick reference data

- $V_{DS} \leq 40$ V
- $R_{DSon} = 4.5$ m Ω (typ)
- $V_F = 658$ mV (typ)
- $S_F = -1.54$ mV/K (typ).

2. Pinning information

Table 1: Pinning - SOT426 and SOT263B, simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)		
2	anode (a)		
3	drain (d)		
4	cathode (k)		
5	source (s)		
mb	mounting base; connected to drain (d)		
		SOT426 (D ² -PAK)	SOT263B (TO-220)



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3. Limiting values

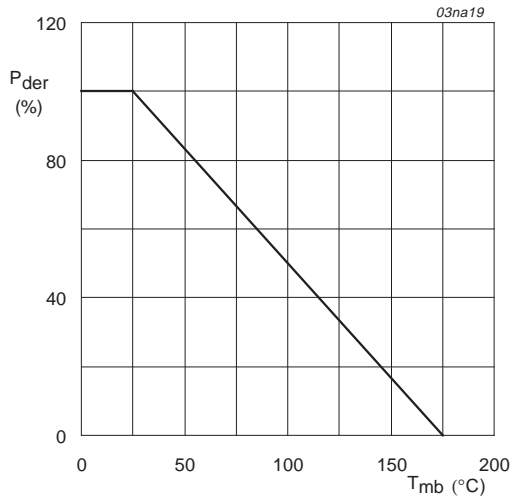
Table 2: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	40	V
V_{DGS}	drain-gate voltage (DC)		-	40	V
V_{GS}	gate-source voltage (DC)		-	±20	V
I_D	drain current (DC)	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ Figure 2 and 3	[1] -	155	A
			[2] -	75	A
		$T_{mb} = 100\text{ °C}; V_{GS} = 10\text{ V};$ Figure 2	[2] -	75	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s};$ Figure 3	-	620	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ Figure 1	-	272	W
$I_{GS(CL)}$	gate-source clamping current	continuous	-	10	mA
		$t_p = 5\text{ ms}; \delta = 0.01$	-	50	mA
T_{stg}	storage temperature		-55	+175	°C
T_j	junction temperature		-55	+175	°C
$V_{isol(FET-TSD)}$	FET to temperature sense diode isolation voltage		-	±100	V
Source-drain diode					
I_{DR}	reverse drain current (DC)	$T_{mb} = 25\text{ °C}$	[1] -	155	A
			[2] -	75	A
I_{DRM}	peak reverse drain current	$T_{mb} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	620	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive avalanche energy	unclamped inductive load; $I_D = 75\text{ A};$ $V_{DS} \leq 40\text{ V}; V_{GS} = 10\text{ V};$ $R_{GS} = 50\text{ }\Omega;$ starting $T_j = 25\text{ °C}$	-	1.46	J
Electrostatic discharge					
V_{esd}	electrostatic discharge voltage, pins 1,3,5	Human Body Model; $C = 100\text{ pF};$ $R = 1.5\text{ k}\Omega$	-	6	kV

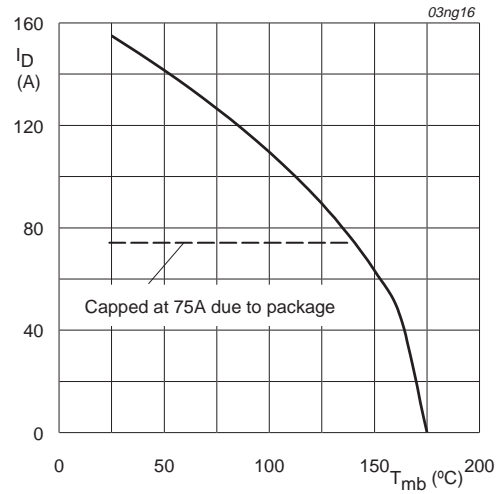
[1] Current is limited by power dissipation chip rating

[2] Continuous current is limited by package.



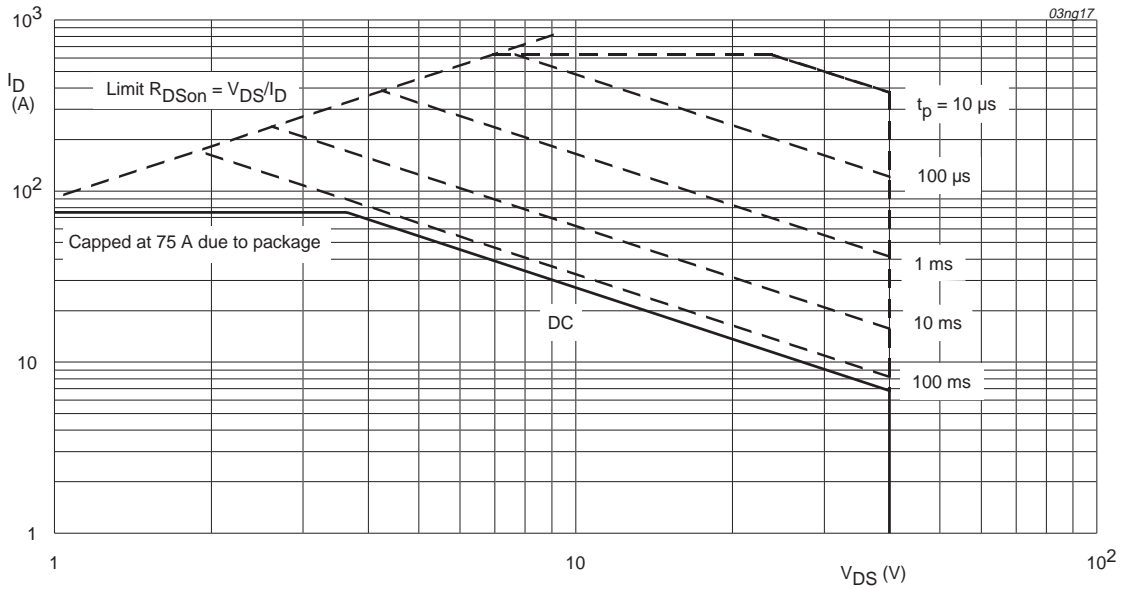
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$V_{GS} \geq 10\text{ V}$

Fig 2. Continuous drain current as a function of mounting base temperature.



$T_{mb} = 25^{\circ}C$; I_{DM} single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

4. Thermal characteristics

Table 3: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient					
	SOT263B	vertical in still air	-	60	-	K/W
	SOT426	mounted on printed circuit board; minimum footprint	-	50	-	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	0.55	K/W

4.1 Transient thermal impedance

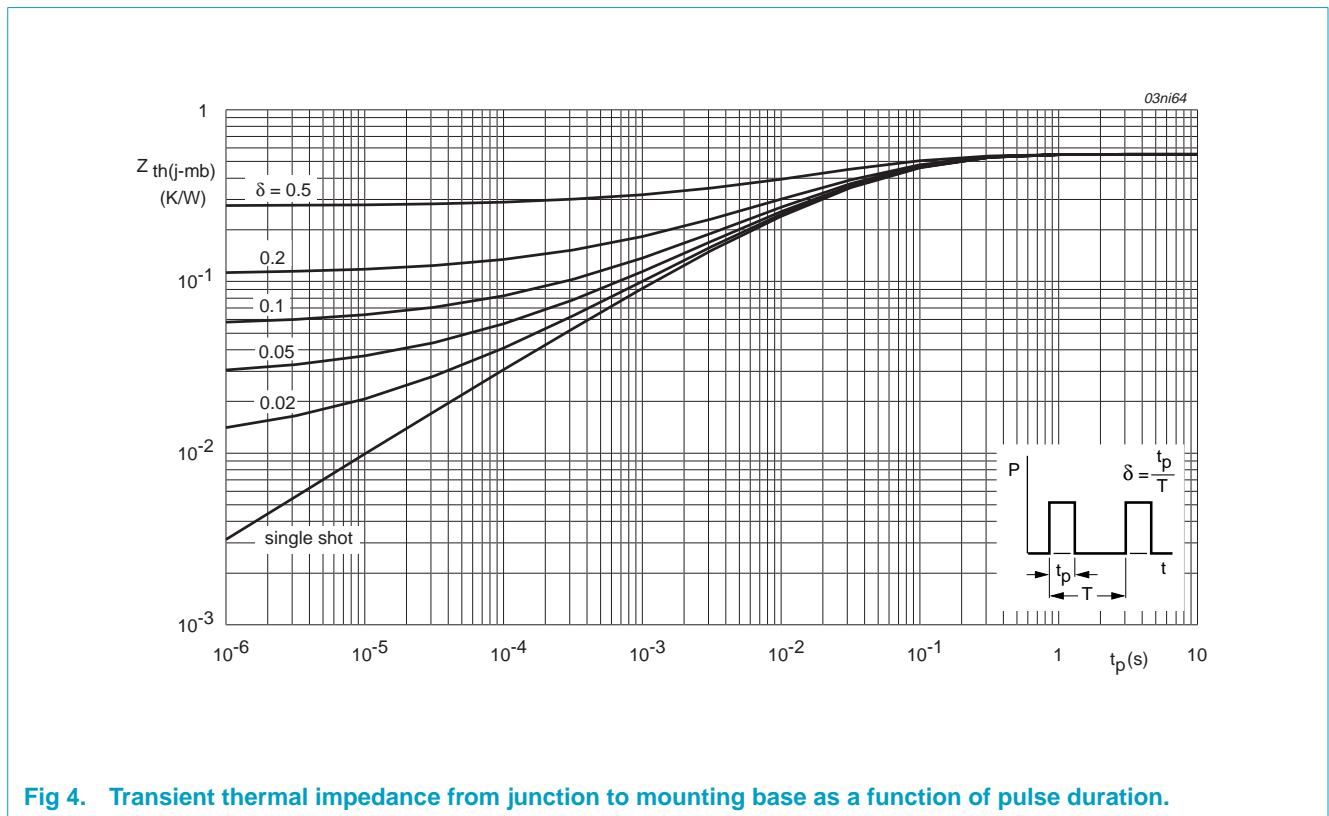


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

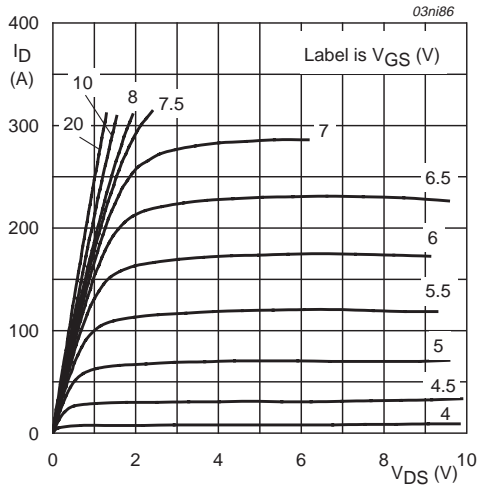
5. Characteristics

Table 4: Characteristics
 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25\text{ mA}; V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ }^\circ\text{C}$	40	-	-	V
		$T_j = -55\text{ }^\circ\text{C}$	36	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}; V_{DS} = V_{GS};$ Figure 9				
		$T_j = 25\text{ }^\circ\text{C}$	2	3	4	V
		$T_j = 175\text{ }^\circ\text{C}$	1	-	-	V
		$T_j = -55\text{ }^\circ\text{C}$	-	-	4.4	V
I_{DSS}	drain-source leakage current	$V_{DS} = 40\text{ V}; V_{GS} = 0\text{ V}$				
		$T_j = 25\text{ }^\circ\text{C}$	-	0.1	10	μA
		$T_j = 175\text{ }^\circ\text{C}$	-	-	250	μA
$V_{(BR)GSS}$	gate-source breakdown voltage	$I_G = \pm 1\text{ mA};$ $-55\text{ }^\circ\text{C} < T_j < 175\text{ }^\circ\text{C}$	20	22	-	V
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 10\text{ V}; V_{DS} = 0\text{ V}$				
		$T_j = 25\text{ }^\circ\text{C}$	-	22	1000	nA
		$T_j = 175\text{ }^\circ\text{C}$	-	-	10	μA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 50\text{ A};$ Figure 7 and 8				
		$T_j = 25\text{ }^\circ\text{C}$	-	4.5	5	m Ω
		$T_j = 175\text{ }^\circ\text{C}$	-	-	9.5	m Ω
V_F	forward voltage, temperature sense diode	$I_F = 250\text{ }\mu\text{A}$	648	658	668	mV
S_F	temperature coefficient temperature sense diode	$I_F = 250\text{ }\mu\text{A};$ $-55\text{ }^\circ\text{C} < T_j < 175\text{ }^\circ\text{C}$	-1.4	-1.54	-1.68	mV/K
V_{hys}	temperature sense diode forward voltage hysteresis	$125\text{ }\mu\text{A} < I_F < 250\text{ }\mu\text{A}$	25	32	50	mV
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	$V_{GS} = 10\text{ V}; V_{DS} = 32\text{ V};$ $I_D = 25\text{ A};$ Figure 14	-	118	-	nC
Q_{gs}	gate-source charge		-	16	-	nC
Q_{gd}	gate-drain (Miller) charge		-	57	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V};$ $f = 1\text{ MHz};$ Figure 12	-	4500	-	pF
C_{oss}	output capacitance		-	1500	-	pF
C_{rss}	reverse transfer capacitance		-	960	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30\text{ V}; R_L = 1.2\text{ }\Omega;$ $V_{GS} = 10\text{ V}; R_G = 10\text{ }\Omega$	-	35	-	nS
t_r	rise time		-	115	-	nS
$t_{d(off)}$	turn-off delay time		-	155	-	nS
t_f	fall time		-	110	-	nS

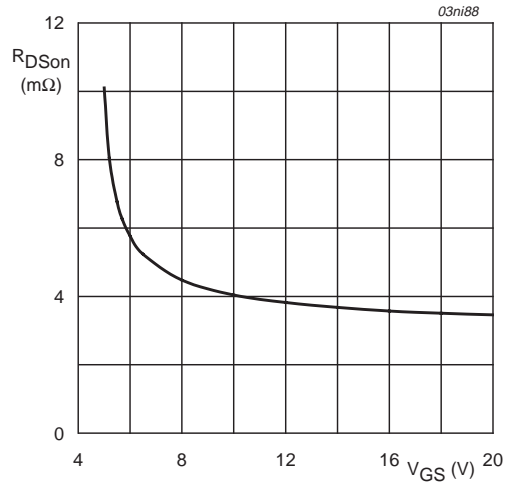
Table 4: Characteristics...continued*T_j = 25 °C unless otherwise specified.*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
L _d	internal drain inductance	measured from upper edge of drain mounting base to centre of die	-	2.5	-	nH
L _s	internal source inductance	measured from source lead to source bond pad	-	7.5	-	nH
Source-drain diode						
V _{SD}	source-drain (diode forward) voltage	I _S = 40 A; V _{GS} = 0 V; Figure 17	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs	-	96	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V	-	224	-	nC



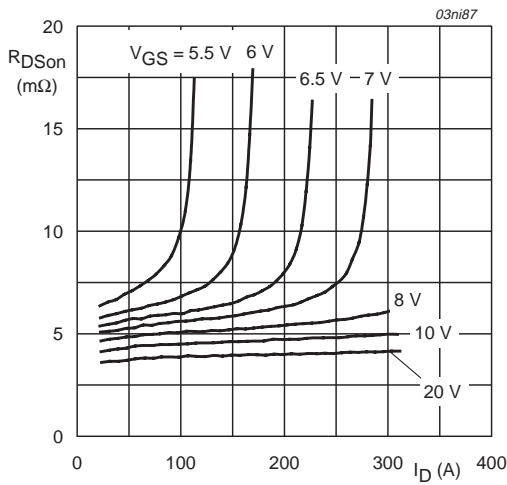
$T_j = 25\text{ }^\circ\text{C}$; $t_p = 300\text{ }\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



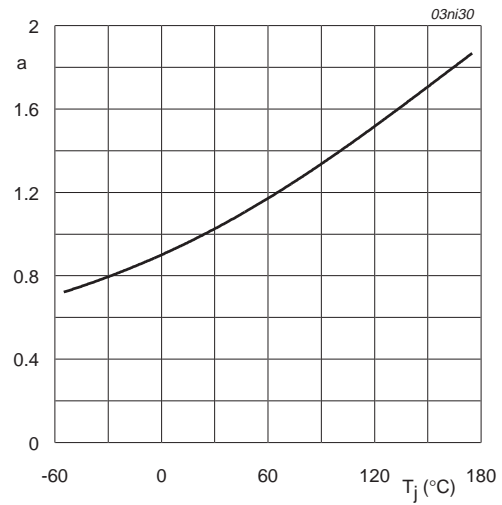
$T_j = 25\text{ }^\circ\text{C}$; $I_D = 50\text{ A}$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values.



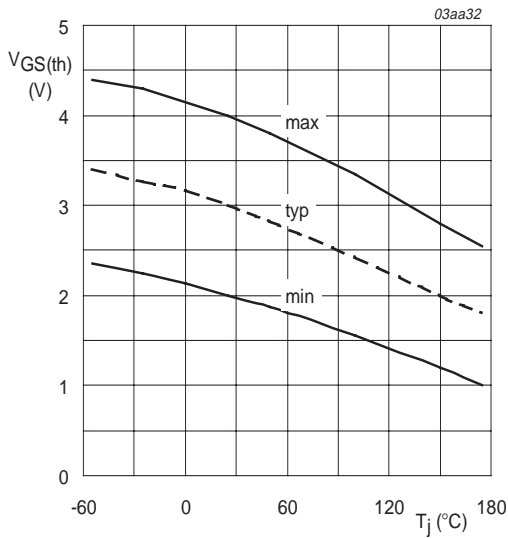
$T_j = 25\text{ }^\circ\text{C}$; $t_p = 300\mu\text{s}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



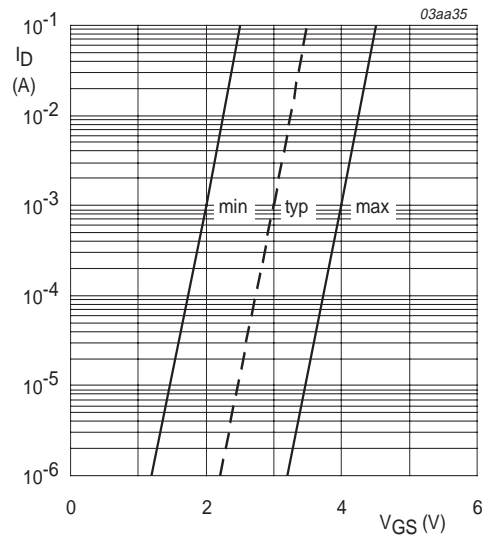
$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



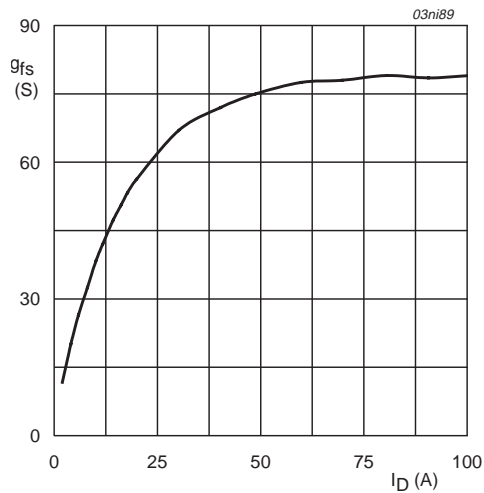
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



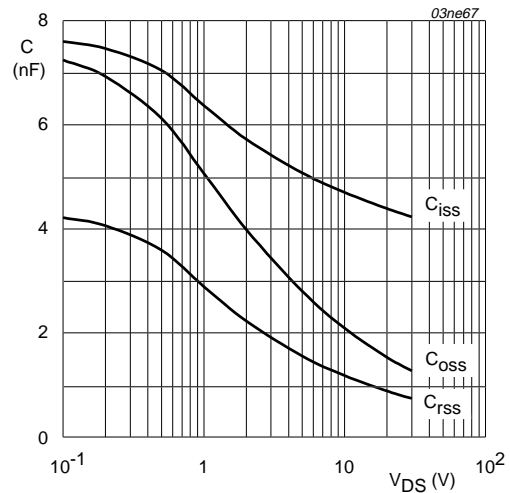
$T_J = 25 \text{ }^\circ\text{C}; V_{DS} = V_{GS}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



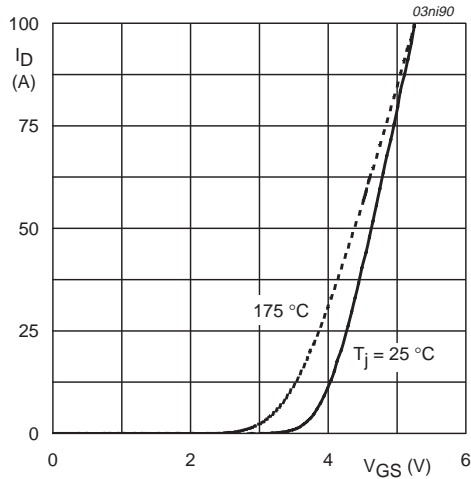
$T_J = 25 \text{ }^\circ\text{C}; V_{DS} = 25 \text{ V}$

Fig 11. Forward transconductance as a function of drain current; typical values.



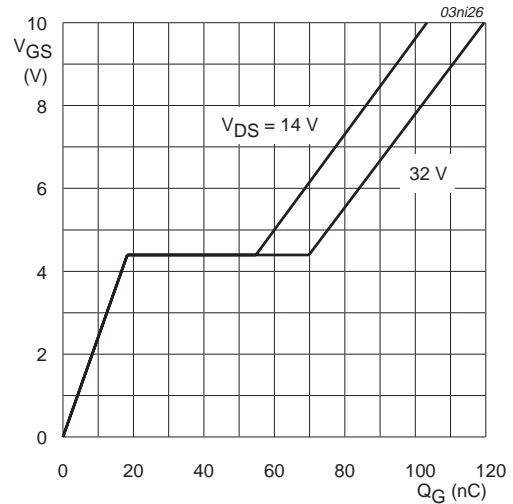
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



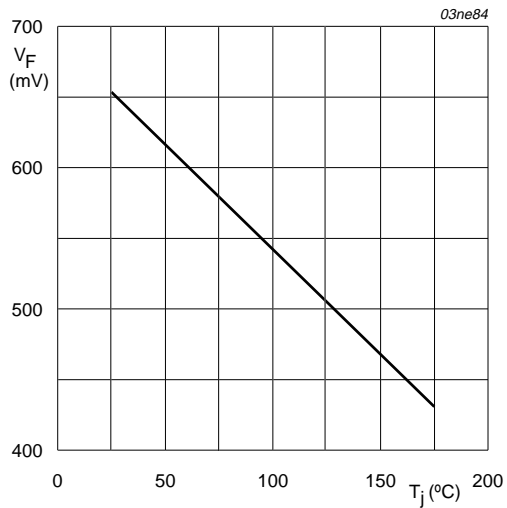
$V_{DS} = 25 \text{ V}$

Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



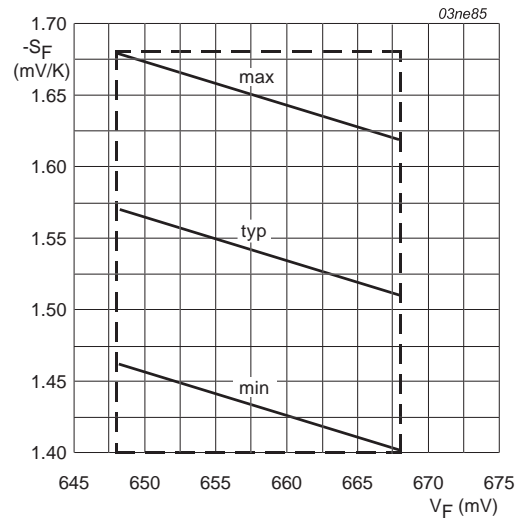
$T_j = 25 \text{ °C}; I_D = 25 \text{ A}$

Fig 14. Gate-source voltage as a function of turn-on gate charge; typical values.



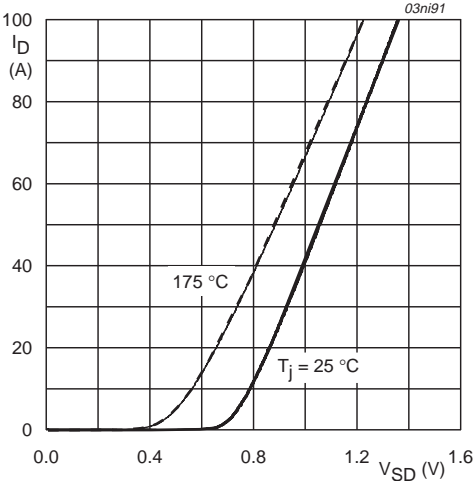
$I_F = 250 \text{ }\mu\text{A}$

Fig 15. Forward voltage of temperature sense diode as a function of junction temperature; typical values.



V_F at $T_j = 25 \text{ °C}; I_F = 250 \text{ }\mu\text{A}$

Fig 16. Temperature coefficient of temperature sense diode as a function of forward voltage; typical values.



$V_{GS} = 0\text{V}$

Fig 17. Reverse diode current as a function of reverse diode voltage; typical values.

6. Package outline

Plastic single-ended surface mounted package (Philips version of D²-PAK); 5 leads
(one lead cropped)

SOT426

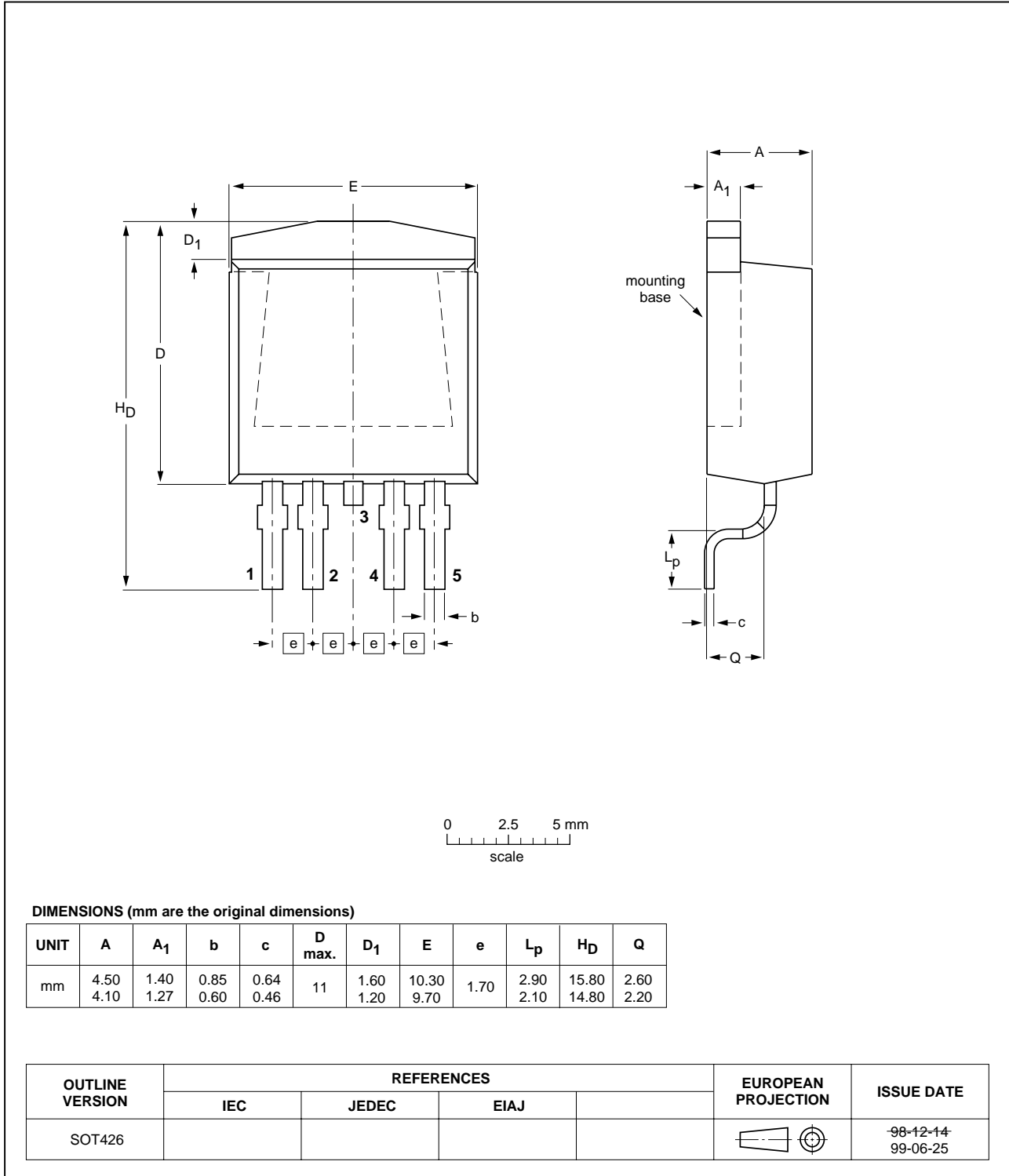


Fig 18. SOT426 (D²-PAK).

Plastic single-ended package; heatsink mounted; 1 mounting hole; 5-lead TO-220

SOT263B

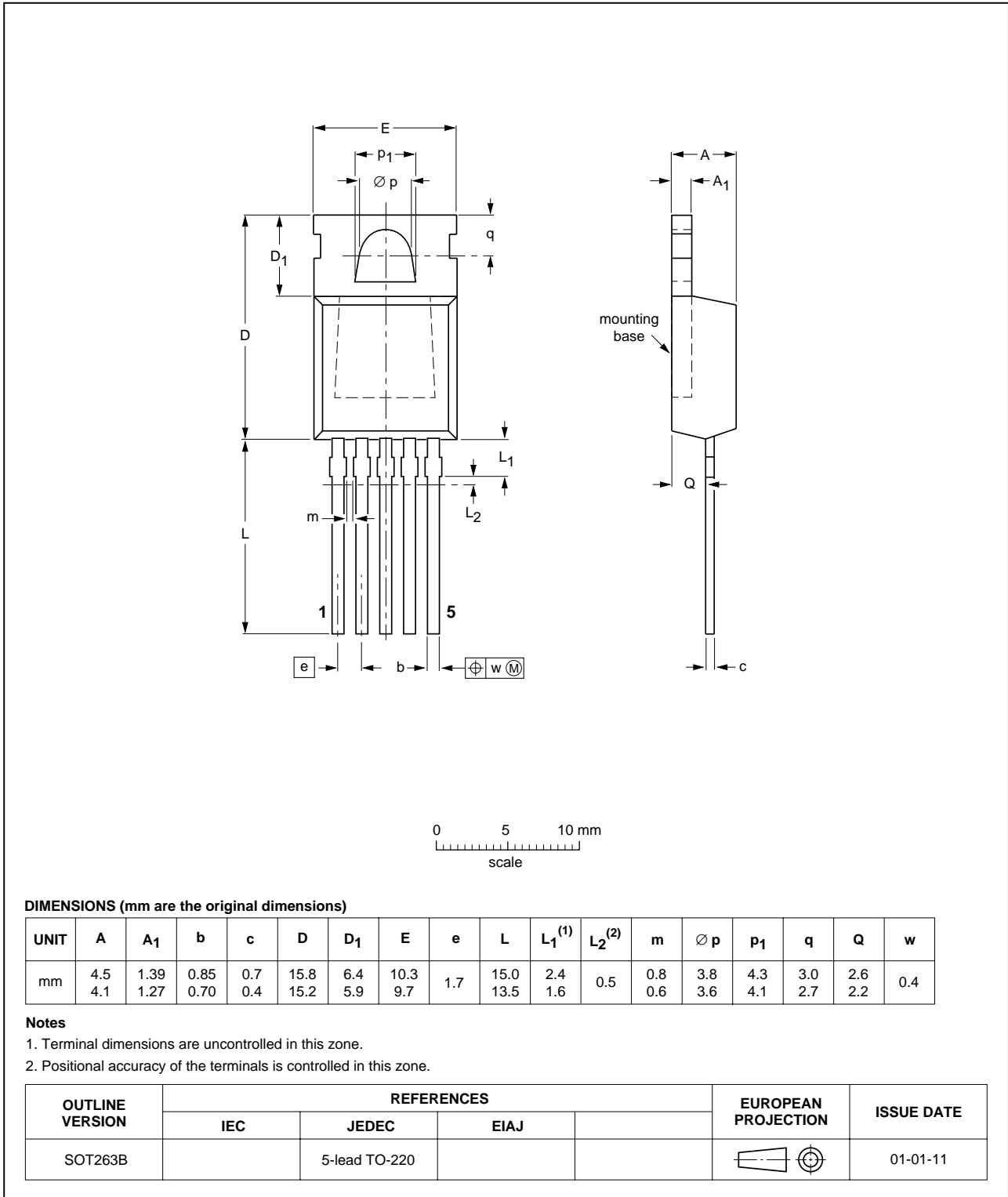
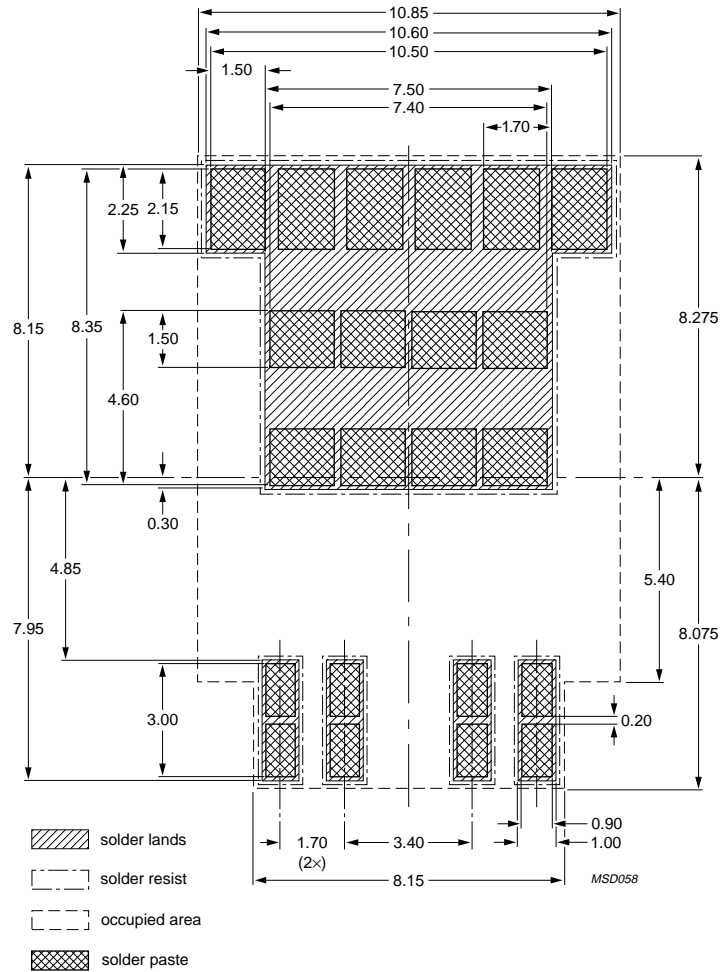


Fig 19. SOT263B (TO-220).

7. Soldering



Dimensions in mm.

Fig 20. Reflow soldering footprint for SOT426.

8. Revision history

Table 5: Revision history

Rev	Date	CPCN	Description
01	20030820	-	Product data; initial version (9397 750 11694)

9. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Date of release: 20 August 2003

Document order number: 9397 750 11694



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